

**Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons**

Kozlovski, Vitali V.; **Korolkov, Oleg**; Lebedev, Alexander A.; **Toompuu, Jana**; **Sleptsuk, Natalja** Silicon Carbide and Related Materials 2019 : 18th International Conference on Silicon Carbide and Related Materials 2019 (ICSCRM 2019), Kyoto, Japan, September 29 - October 4, 2019 2020 / p. 231-236 <https://doi.org/10.4028/www.scientific.net/MSF.1004.231> Conference Proceedings at Scopus Article at Scopus

**Dependence of the carrier removal rate in 4H-SiC PN structures on irradiation temperature**

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**Influence of the proton irradiation temperature on the characteristics of high-power high-voltage silicon carbide schottky diodes**

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